Surface Mount Schottky Power Rectifier

SMA Power Surface Mount Package

MBRA1H100, NRVBA1H100, NRVBA1H100N

Employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity diodes in surface mount applications where compact size and weight are critical to the system.

Features

- Small Compact Surface Mountable Package with J-Bent Leads
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- Low Forward Voltage Drop
- Guardring for Stress Protection
- NRVBA Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable*
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 70 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Polarity: Cathode Lead Indicated by Polarity Band
- ESD Ratings:
 - ♦ Machine Model = C
 - ♦ Human Body Model = 3B
- Device Meets MSL 1 Requirements



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SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES, 100 VOLTS



SMA CASE 403D



MARKING DIAGRAMS



A110 = Device Code

A = Assembly Location**

Y = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRA1H100T3G	SMA (Pb-Free)	5,000 / Tape & Reel
NRVBA1H100T3G*	SMA (Pb-Free)	5,000 / Tape & Reel
NRVBA1H100NT3G*	SMA (Pb-Free)	5,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

^{**}The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejecter pin), the front side assembly code may be blank.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	V
Average Rectified Forward Current $(T_L = 167^{\circ}C)$	I _O	1.0	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	50	А
Storage and Operating Junction Temperature Range (Note 1)	T _{stg} , T _J	-65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Note 2)	Ψ_{JCL}	14	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	75	°C/W
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{ heta JA}$	280	°C/W

Mounted with 700 mm² copper pad size (Approximately 1 in²) 1 oz FR4 Board.
 Mounted with pad size approximately 6 mm² copper, 1 oz FR4 Board.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 4) ($I_F = 1.0 \text{ A}, T_J = 25^{\circ}\text{C}$) ($I_F = 2.0 \text{ A}, T_J = 25^{\circ}\text{C}$) ($I_F = 1.0 \text{ A}, T_J = 125^{\circ}\text{C}$) ($I_F = 2.0 \text{ A}, T_J = 125^{\circ}\text{C}$)	V _F	0.76 0.84 0.61 0.68	V
Maximum Instantaneous Reverse Current (Note 4) (Rated dc Voltage, $T_J = 25^{\circ}C$) (Rated dc Voltage, $T_J = 125^{\circ}C$)	I _R	40 0.5	μ A mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

^{4.} Pulse Test: Pulse Width ≤ 380 μs, Duty Cycle ≤ 2.0%.

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TYPICAL CHARACTERISTICS

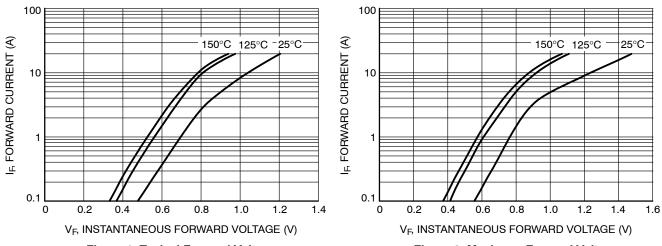


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

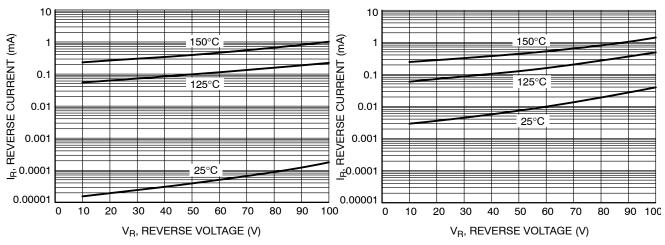
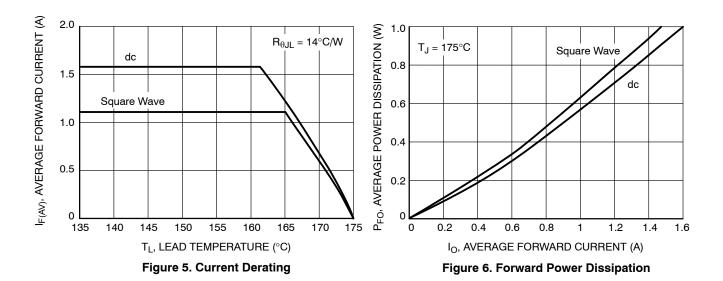


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current



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TYPICAL CHARACTERISTICS

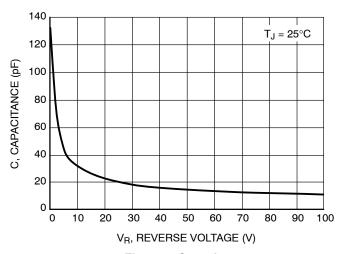


Figure 7. Capacitance

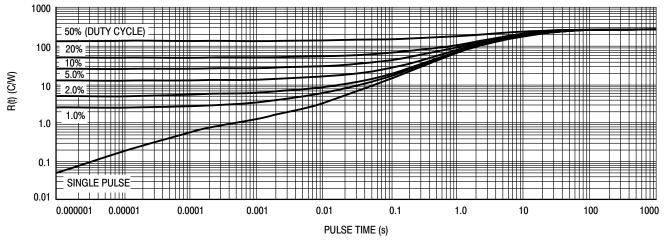


Figure 8. Thermal Response, Junction-to-Ambient (6 mm² pad)

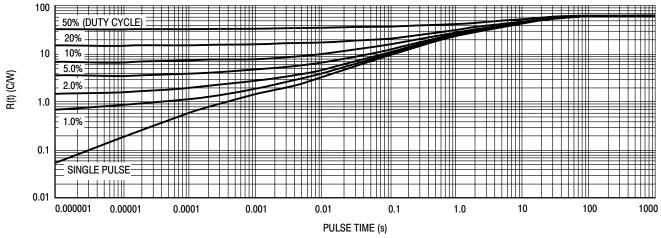


Figure 9. Thermal Response, Junction-to-Ambient (1 in² pad)







STYLE 1 STYLE 2

SCALE 1:1

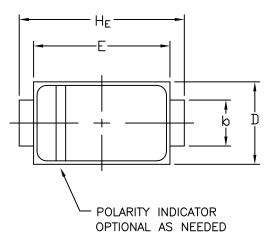


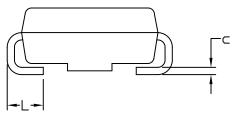
DATE 22 OCT 2021

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION 6 SHALL BE MEASURED WITHIN DIMENSION L.

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	1.97	2.10	2.20	0.078	0.083	0.087
A1	0.05	0.10	0.20	0.002	0.004	0.008
b	1.27	1.45	1.63	0.050	0.057	0.064
С	0.15	0.28	0.41	0.006	0.011	0.016
D	2.29	2.60	2.92	0.090	0.103	0.115
Ε	4.06	4.32	4.57	0.160	0.170	0.180
HE	4.83	5.21	5.59	0.190	0.205	0.220
L	0.76	1.14	1.52	0.030	0.045	0.060

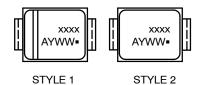




STYLE 1: STYLE 2: PIN 1. CATHODE (POLARITY BAND) NO POLARITY 2. ANODE

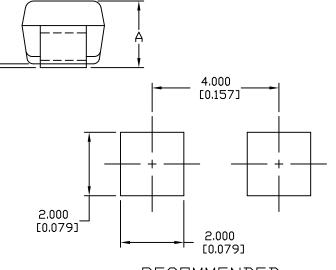
DDE (POLARITY BAND) NO POLARIT E

GENERIC MARKING DIAGRAM*



xxxx = Specific Device Code A = Assembly Location

Y = Year WW = Work Week ■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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